

# MOSFET – Power, Single N-Channel

## 100 V, 26 mΩ, 28 A

### NVMFS027N10MCL

#### Features

- Small Footprint (5x6 mm) for Compact Design
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low  $Q_G$  and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualified and PPAP Capable
- NVMFWS027N10MCL – Wettable Flank Products
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

| Parameter   | Symbol   | Value                     | Unit             |
|---|--|---------------------------|------------------|
| Drain-to-Source Voltage   | $V_{DSS}$                                      | 100                       | V                |
| Gate-to-Source Voltage  | $V_{GS}$                                       | $\pm 20$                  | V                |
| Continuous Drain Current $R_{\theta JC}$ (Notes 1, 3)                         | Steady State                                   | $T_C = 25^\circ\text{C}$  | $I_D$ 28 A       |
|   |  | $T_C = 100^\circ\text{C}$ | 20               |
| Power Dissipation $R_{\theta JC}$ (Note 1)                                    | Steady State                                   | $T_C = 25^\circ\text{C}$  | $P_D$ 46 W       |
|   |  | $T_C = 100^\circ\text{C}$ | 23               |
| Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2, 3)                      | Steady State                                   | $T_A = 25^\circ\text{C}$  | $I_D$ 7.9 A      |
|   |  | $T_A = 100^\circ\text{C}$ | 5.6              |
| Power Dissipation $R_{\theta JA}$ (Notes 1, 2)                                | Steady State                                   | $T_A = 25^\circ\text{C}$  | $P_D$ 3.5 W      |
|   |  | $T_A = 100^\circ\text{C}$ | 1.8              |
| Pulsed Drain Current  | $T_A = 25^\circ\text{C}, t_p = 10 \mu\text{s}$ | $I_{DM}$ 137              | A                |
| Operating Junction and Storage Temperature Range                              | $T_J, T_{stg}$                                 | -55 to +175               | $^\circ\text{C}$ |
| Source Current (Body Diode)   | $I_S$  | 35                        | A                |
| Single Pulse Drain-to-Source Avalanche Energy ( $I_{L(pk)} = 1.3 \text{ A}$ ) | $E_{AS}$                                       | 414                       | mJ               |
| Lead Temperature for Soldering Purposes (1/8" from case for 10 s)             | $T_L$  | 260                       | $^\circ\text{C}$ |

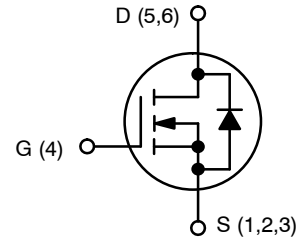
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE MAXIMUM RATINGS

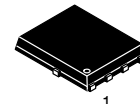
| Parameter                                   | Symbol          | Value | Unit                      |
|---|-----------------|-------|---------------------------|
| Junction-to-Case – Steady State (Note 1)    | $R_{\theta JC}$ | 3.3   | $^\circ\text{C}/\text{W}$ |
| Junction-to-Ambient – Steady State (Note 2) | $R_{\theta JA}$ | 42.4  |                           |

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using a 650 mm<sup>2</sup>, 2 oz. Cu pad.
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

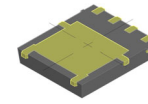
| $V_{(BR)DSS}$ | $R_{DS(ON) MAX}$ | $I_D MAX$ |
|---------------|------------------|-----------|
| 100 V         | 26 mΩ @ 10 V     | 28 A      |
|               | 35 mΩ @ 4.5 V    |           |



N-CHANNEL MOSFET

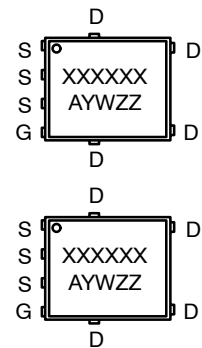


DFN5  
CASE 488AA  
STYLE 1



DFNW5  
(for WF Version)  
CASE 507BA

#### MARKING DIAGRAM



XXXXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
W = Work Week  
ZZ = Lot Traceability

#### ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 5 of this data sheet.

# NVMFS027N10MCL

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test Condition | Min | Typ | Max | Unit |
|-----------|--------|----------------|-----|-----|-----|------|
|-----------|--------|----------------|-----|-----|-----|------|

### OFF CHARACTERISTICS

|   |                   |   |                           |    |     |               |
|---|-------------------|---|---------------------------|----|-----|---------------|
| Drain-to-Source Breakdown Voltage                         | $V_{(BR)DSS}$     | $V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$ | 100                       |    |     | V             |
| Drain-to-Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ |   |                           | 53 |     | mV/°C         |
| Zero Gate Voltage Drain Current                           | $I_{DSS}$         | $V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}$  | $T_J = 25^\circ\text{C}$  |    | 1.0 | $\mu\text{A}$ |
|   |                   |   | $T_J = 125^\circ\text{C}$ |    | 100 |               |
| Gate-to-Source Leakage Current                            | $I_{GSS}$         | $V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$   |                           |    | 100 | nA            |

### ON CHARACTERISTICS

|                                   |                  |  |                    |    |    |            |
|-----------------------------------|------------------|--|--------------------|----|----|------------|
| Gate Threshold Voltage            | $V_{GS(TH)}$     | $V_{GS} = V_{DS}, I_D = 38\ \mu\text{A}$ | 1                  |    | 3  | V          |
| Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ |  |                    | -6 |    | mV/°C      |
| Drain-to-Source On Resistance     | $R_{DS(on)}$     | $V_{GS} = 10\text{ V}$                   | $I_D = 7\text{ A}$ | 21 | 26 | m $\Omega$ |
|                                   |                  | $V_{GS} = 4.5\text{ V}$                  | $I_D = 5\text{ A}$ | 28 | 35 |            |
| Forward Transconductance          | $g_{FS}$         | $V_{DS} = 10\text{ V}, I_D = 7\text{ A}$ |                    | 25 |    | S          |

### CHARGES, CAPACITANCES & GATE RESISTANCE

|                              |              |   |  |      |  |          |
|------------------------------|--------------|---|--|------|--|----------|
| Input Capacitance            | $C_{ISS}$    | $V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = 50\text{ V}$   |  | 800  |  | pF       |
| Output Capacitance           | $C_{OSS}$    |   |  | 300  |  |          |
| Reverse Transfer Capacitance | $C_{RSS}$    |   |  | 4    |  |          |
| Gate Resistance              | $R_G$        |   |  | 0.41 |  | $\Omega$ |
| Total Gate Charge            | $Q_{G(TOT)}$ | $V_{GS} = 4.5\text{ V}, V_{DS} = 50\text{ V}; I_D = 7\text{ A}$ |  | 5.5  |  | nC       |
| Total Gate Charge            | $Q_{G(TOT)}$ | $V_{GS} = 10\text{ V}, V_{DS} = 50\text{ V}; I_D = 7\text{ A}$  |  | 11.5 |  | nC       |
| Threshold Gate Charge        | $Q_{G(TH)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 50\text{ V}; I_D = 7\text{ A}$  |  | 1.3  |  | nC       |
| Gate-to-Source Charge        | $Q_{GS}$     |   |  | 2.1  |  |          |
| Gate-to-Drain Charge         | $Q_{GD}$     |   |  | 1.2  |  |          |
| Plateau Voltage              | $V_{GP}$     |   |  | 2.5  |  | V        |
| Output Charge                | $Q_{OSS}$    | $V_{GS} = 0\text{ V}, V_{DS} = 50\text{ V}$                     |  | 87   |  | nC       |

### SWITCHING CHARACTERISTICS (Note 4)

|                     |              |   |  |     |  |    |
|---------------------|--------------|---|--|-----|--|----|
| Turn-On Delay Time  | $t_{d(ON)}$  | $V_{GS} = 10\text{ V}, V_{DS} = 50\text{ V}, I_D = 7\text{ A}, R_G = 6.0\ \Omega$ |  | 7.4 |  | ns |
| Rise Time           | $t_r$        |   |  | 2   |  |    |
| Turn-Off Delay Time | $t_{d(OFF)}$ |   |  | 19  |  |    |
| Fall Time           | $t_f$        |   |  | 2.9 |  |    |

### DRAIN-SOURCE DIODE CHARACTERISTICS

|                         |          |   |  |      |     |    |
|-------------------------|----------|---|--|------|-----|----|
| Forward Diode Voltage   | $V_{SD}$ | $V_{GS} = 0\text{ V}, I_S = 7\text{ A}, T_J = 25^\circ\text{C}$             |  | 0.84 | 1.3 | V  |
|                         |          | $V_{GS} = 0\text{ V}, I_S = 7\text{ A}, T_J = 125^\circ\text{C}$            |  | 0.73 |     |    |
| Reverse Recovery Time   | $t_{RR}$ | $V_{GS} = 0\text{ V}, dI_S/dt = 100\text{ A}/\mu\text{s}, I_S = 3\text{ A}$ |  | 28   |     | ns |
| Reverse Recovery Charge | $Q_{RR}$ |   |  | 17   |     | nC |
| Charge Time             | $t_a$    |   |  | 13.9 |     | ns |
| Discharge Time          | $t_b$    |   |  | 14.2 |     | ns |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

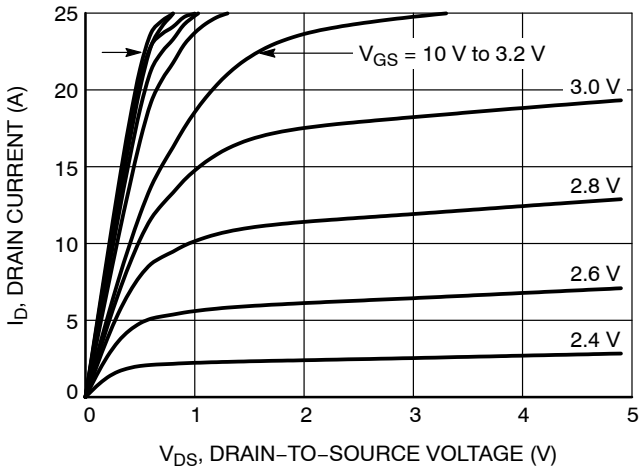


Figure 1. On-Region Characteristics

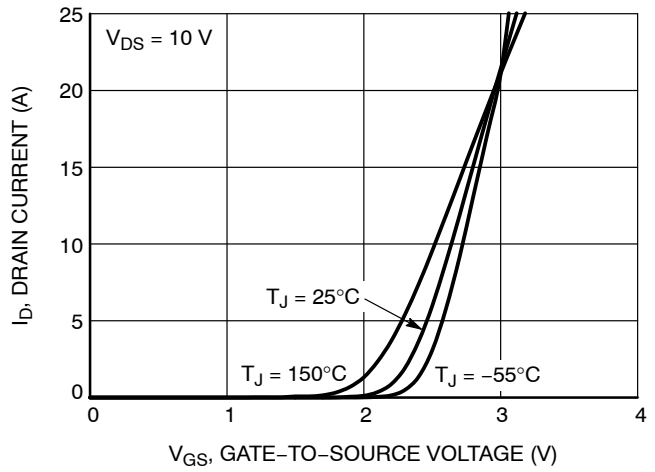


Figure 2. Transfer Characteristics

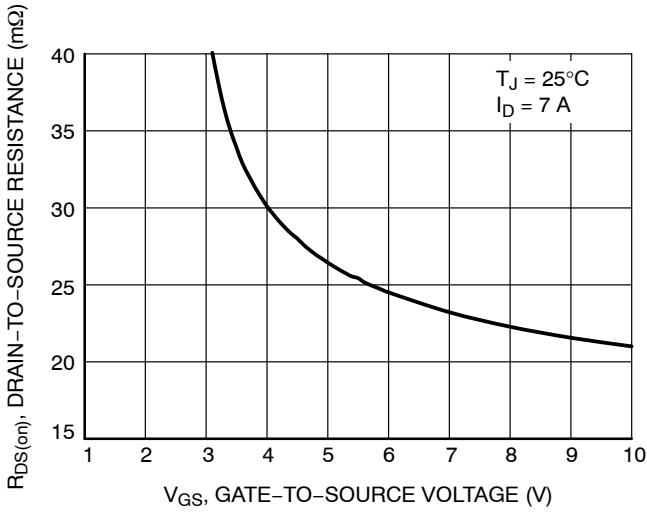


Figure 3. On-Resistance vs. Gate-to-Source Voltage

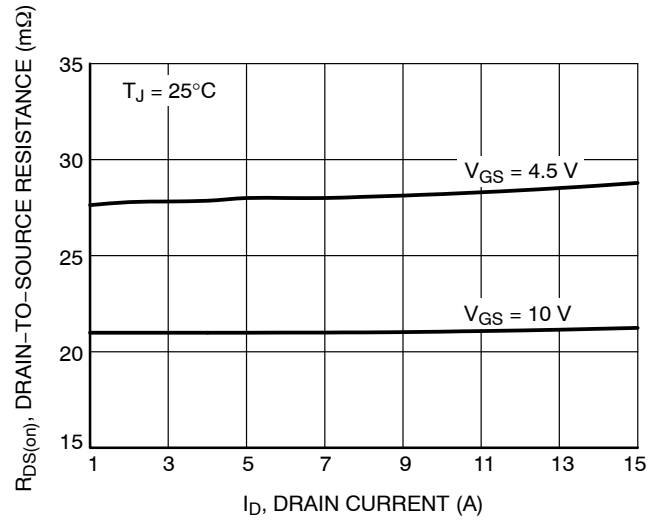


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

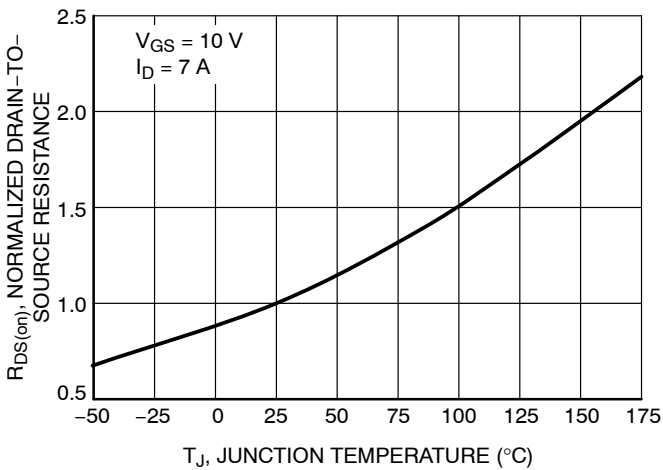


Figure 5. On-Resistance Variation with Temperature

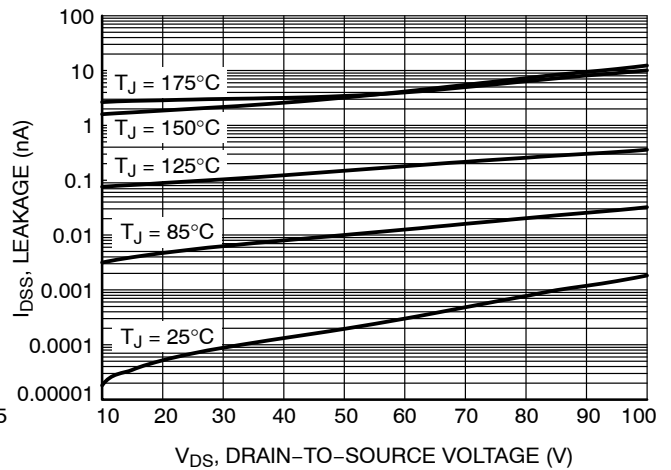


Figure 6. Drain-to-Source Leakage Current vs. Voltage

# NVMFS027N10MCL

## TYPICAL CHARACTERISTICS

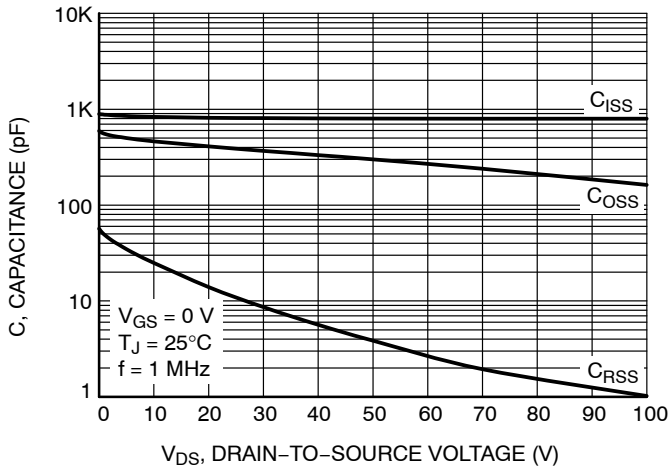


Figure 7. Capacitance Variation

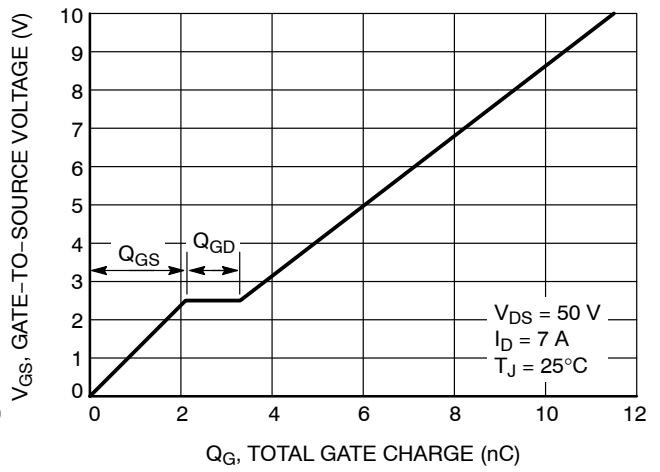


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

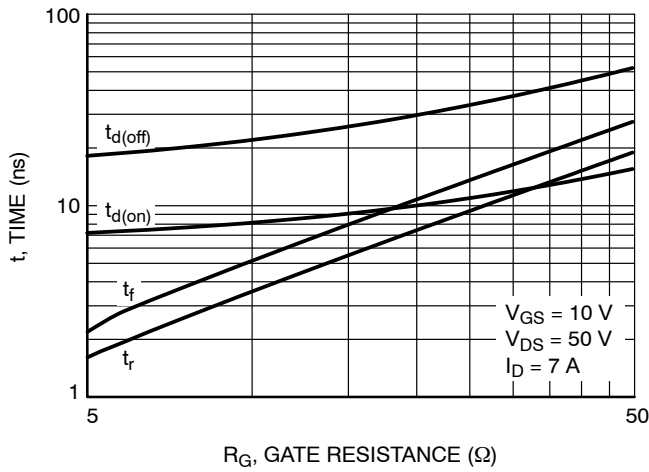


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

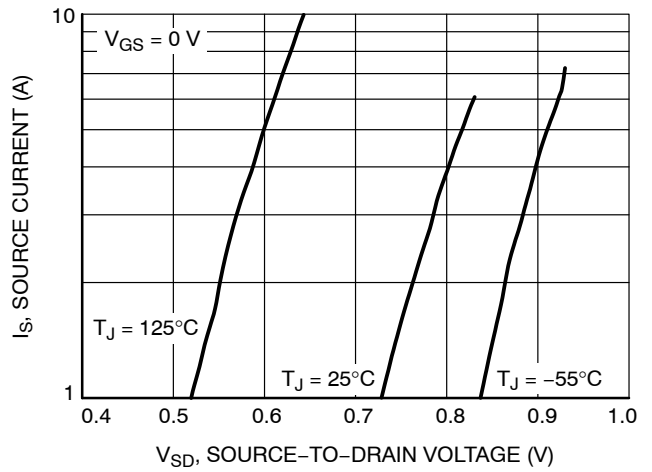


Figure 10. Diode Forward Voltage vs. Current

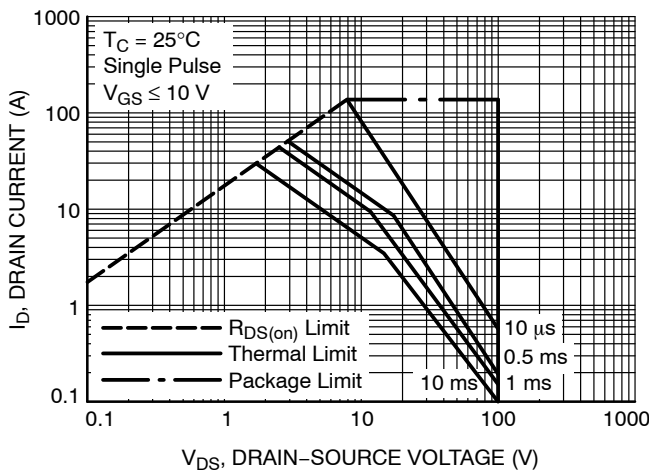


Figure 11. Safe Operating Area

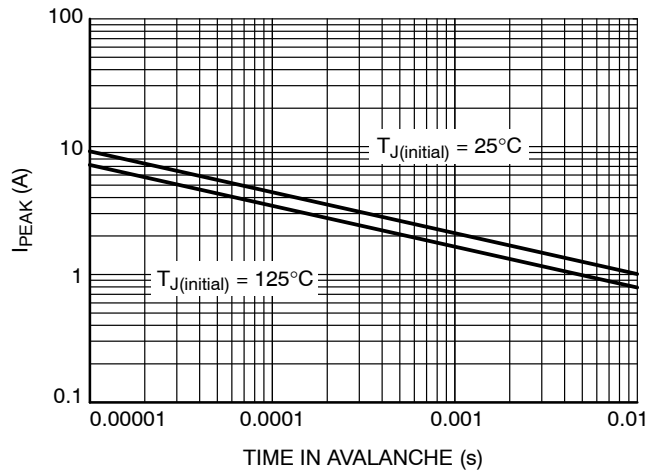


Figure 12. Maximum Drain Current vs. Time in Avalanche

# NVMFS027N10MCL

## TYPICAL CHARACTERISTICS

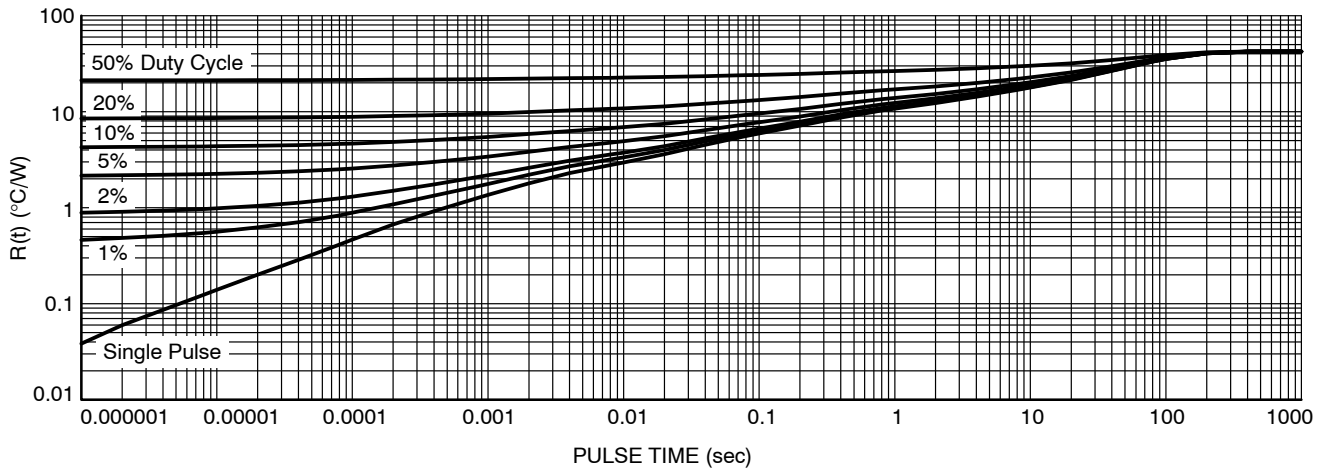


Figure 13. Thermal Response

### DEVICE ORDERING INFORMATION

| Device             | Marking | Package                           | Shipping <sup>†</sup> |
|--------------------|---------|-----------------------------------|-----------------------|
| NVMFS027N10MCLT1G  | 027L10  | DFN5<br>(Pb-Free)                 | 1500 / Tape & Reel    |
| NVMFWS027N10MCLT1G | 027W10  | DFN5<br>(Wettable Flank, Pb-Free) | 1500 / Tape & Reel    |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

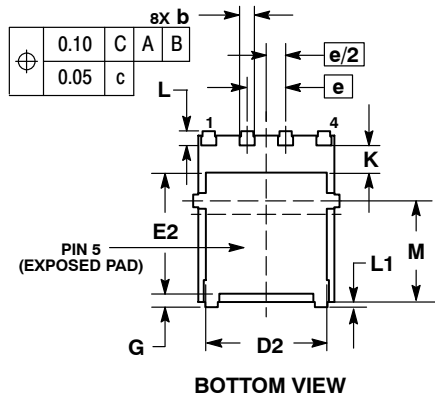
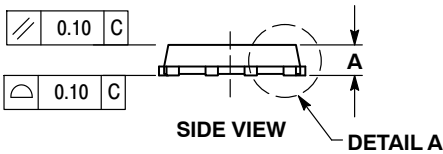
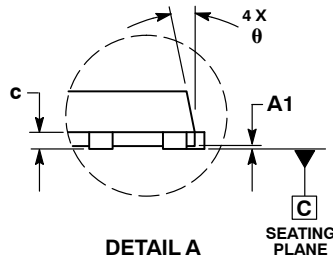
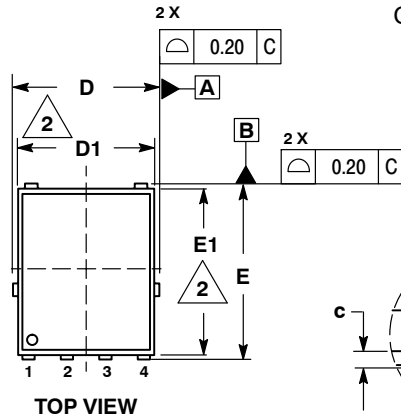
# NVMFS027N10MCL

## PACKAGE DIMENSIONS

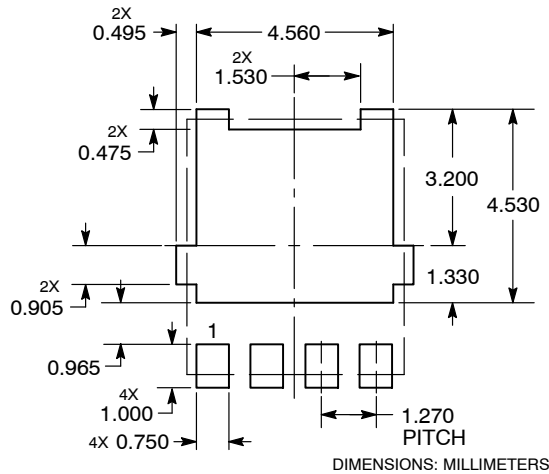
DFN5 5x6, 1.27P  
(SO-8FL)  
CASE 488AA  
ISSUE N

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

| DIM | MILLIMETERS |       |      |
|-----|-------------|-------|------|
|     | MIN         | NOM   | MAX  |
| A   | 0.90        | 1.00  | 1.10 |
| A1  | 0.00        | ---   | 0.05 |
| b   | 0.33        | 0.41  | 0.51 |
| c   | 0.23        | 0.28  | 0.33 |
| D   | 5.00        | 5.15  | 5.30 |
| D1  | 4.70        | 4.90  | 5.10 |
| D2  | 3.80        | 4.00  | 4.20 |
| E   | 6.00        | 6.15  | 6.30 |
| E1  | 5.70        | 5.90  | 6.10 |
| E2  | 3.45        | 3.65  | 3.85 |
| e   | 1.27 BSC    |       |      |
| G   | 0.51        | 0.575 | 0.71 |
| K   | 1.20        | 1.35  | 1.50 |
| L   | 0.51        | 0.575 | 0.71 |
| L1  | 0.125 REF   |       |      |
| M   | 3.00        | 3.40  | 3.80 |
| θ   | 0°          | ---   | 12°  |



### RECOMMENDED SOLDERING FOOTPRINT\*



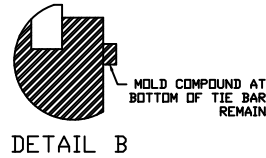
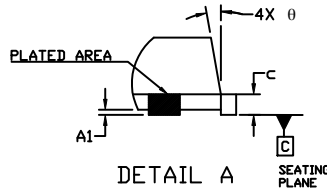
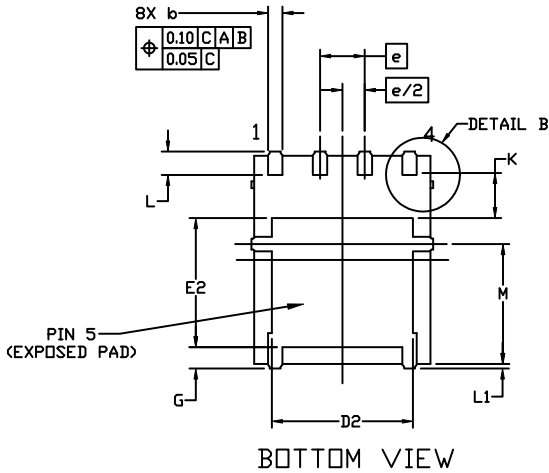
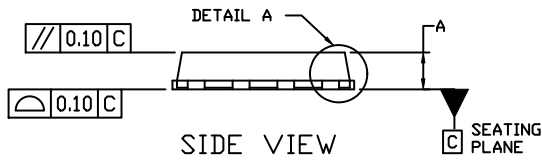
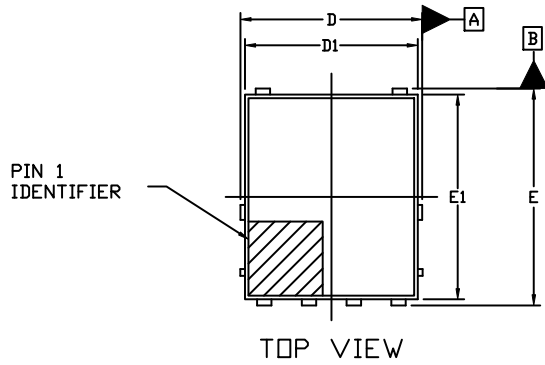
- STYLE 1:  
PIN 1. SOURCE  
2. SOURCE  
3. SOURCE  
4. GATE  
5. DRAIN

\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# NVMFS027N10MCL

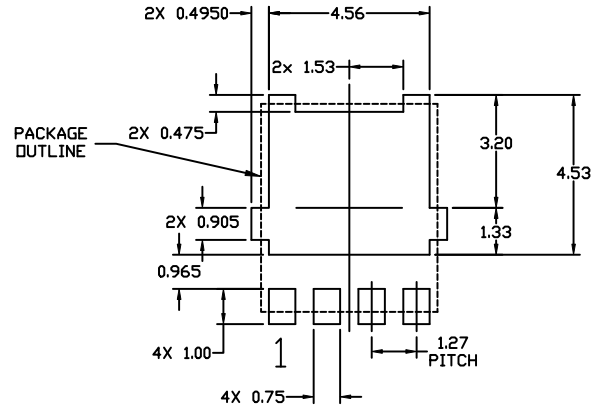
## PACKAGE DIMENSIONS

### DFNW5 5x6 (FULL-CUT SO8FL WF) CASE 507BA ISSUE A



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
  2. CONTROLLING DIMENSION: MILLIMETERS
  3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
  4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.

| MILLIMETERS |           |       |      |
|-------------|-----------|-------|------|
| DIM         | MIN.      | NOM.  | MAX. |
| A           | 0.90      | 1.00  | 1.10 |
| A1          | 0.00      | ---   | 0.05 |
| b           | 0.33      | 0.41  | 0.51 |
| c           | 0.23      | 0.28  | 0.33 |
| D           | 5.00      | 5.15  | 5.30 |
| D1          | 4.70      | 4.90  | 5.10 |
| D2          | 3.80      | 4.00  | 4.20 |
| E           | 6.00      | 6.15  | 6.30 |
| E1          | 5.70      | 5.90  | 6.10 |
| E2          | 3.45      | 3.65  | 3.85 |
| e           | 1.27 BSC  |       |      |
| G           | 0.51      | 0.575 | 0.71 |
| K           | 1.20      | 1.35  | 1.50 |
| L           | 0.51      | 0.575 | 0.71 |
| L1          | 0.150 REF |       |      |
| M           | 3.00      | 3.40  | 3.80 |
| $\theta$    | 0°        | ---   | 12°  |



### RECOMMENDED MOUNTING FOOTPRINT

- \* For additional information on our Pb-Free strategy and soldering details, please download the ION Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# NVMFS027N10MCL

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